

In the claims:

Please substitute the following claims 2, 3, 6, 8, 20 and 35 for the like-numbered claim as originally filed. A marked up copy of this claim showing the current changes is attached as an appendix to this amendment.

fig. 24C  
93  
2. (Amended) A vertical transistor as recited in claim 1, further including isolation material adjacent said layer of insulator and surrounding said vertical transistor, said isolation material being selectively etchable relative to said layer of insulator.

3. (Amended) A vertical transistor as recited in claim 2, further including

4 a contact formed in an opening in said isolation material adjacent [said <sup>layer of</sup> insulator] to a conductive region at an end of said pillar.

94  
fig. 24C,  
38C  
6. (Amended) An integrated circuit device including isolation material surrounding transistor locations in a substrate,

vertical field effect transistors formed at said transistor locations and having a gate electrode structure formed in a trench,

a layer of insulator material in said trench between said isolation material and said gate electrode structure, said isolation material being selectively etchable relative to said layer of insulator and

a contact opening formed along an interface of said layer of insulator material and said isolation material.

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8. (Amended) A device as recited in claim 6, further including

4 a contact formed in said contact opening in said isolation material adjacent said insulator <sub>material</sub> and